

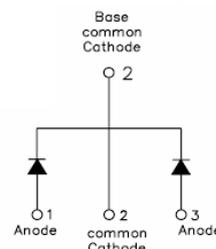
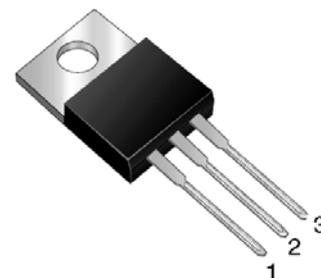
MBR30100CTP SCHOTTKY RECTIFIER

Applications:

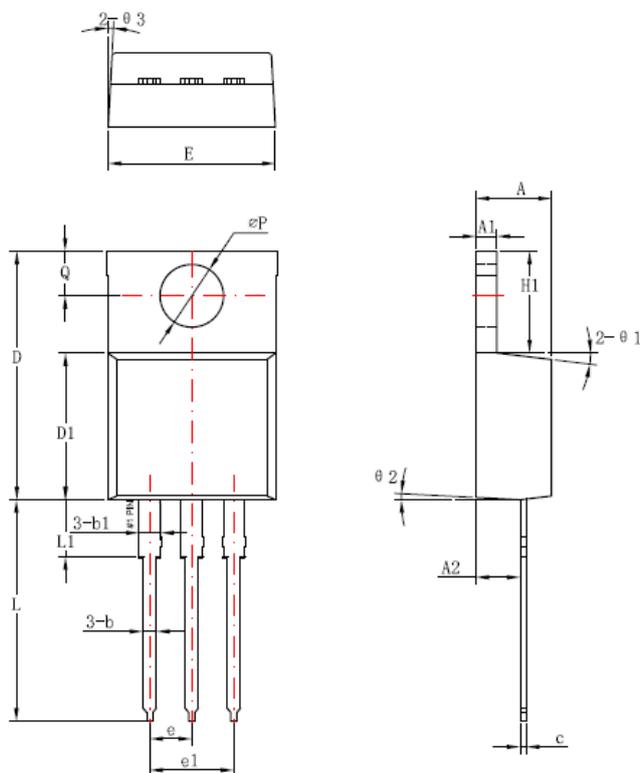
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions: In mm



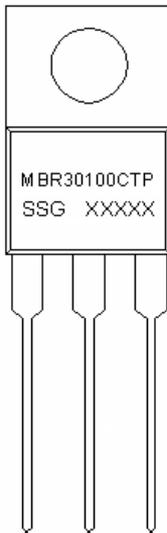
Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

TO-220AB

Technical Data
Data Sheet N1289, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
30 = Forward Current (30A)
100 = Reverse Voltage (100V)
CTP = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR30100CTP	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current(per device)	$I_{F(AV)}$	50% duty cycle @ $T_C = 133^\circ\text{C}$, rectangular wave form	30	A
Peak Repetitive Forward Current(per leg)	I_{FRM}	Rated V_R square wave, 20KHz $T_C = 133^\circ\text{C}$	20	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V _{F1}	@ 15 A, Pulse, T _J = 25 °C	0.85	V
	V _{F2}	@ 15 A, Pulse, T _J = 125 °C	0.70	V
Reverse Current (per leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.00	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	6.0	mA
Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	400	pF
Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	2.0	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θJA}	DC operation	50	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased	0.50	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

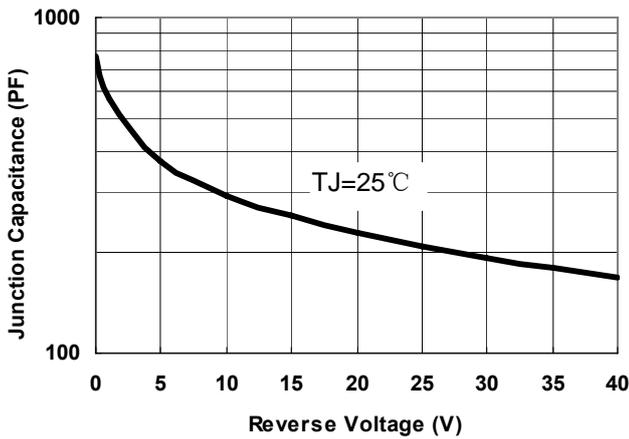


Fig.1-Typical Junction Capacitance

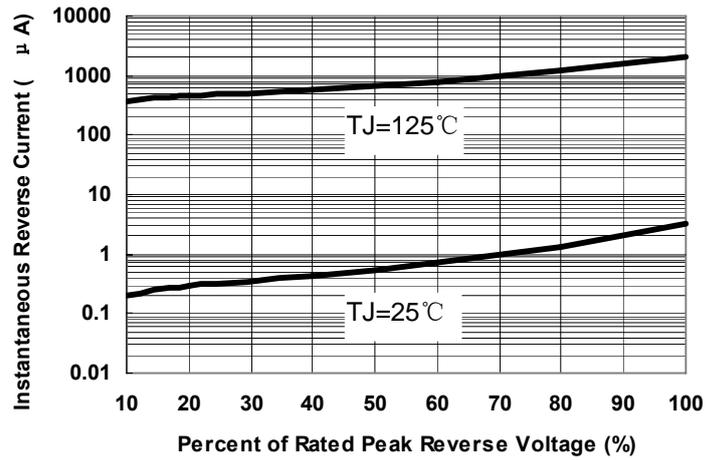


Fig.2-Typical Reverse Characteristics

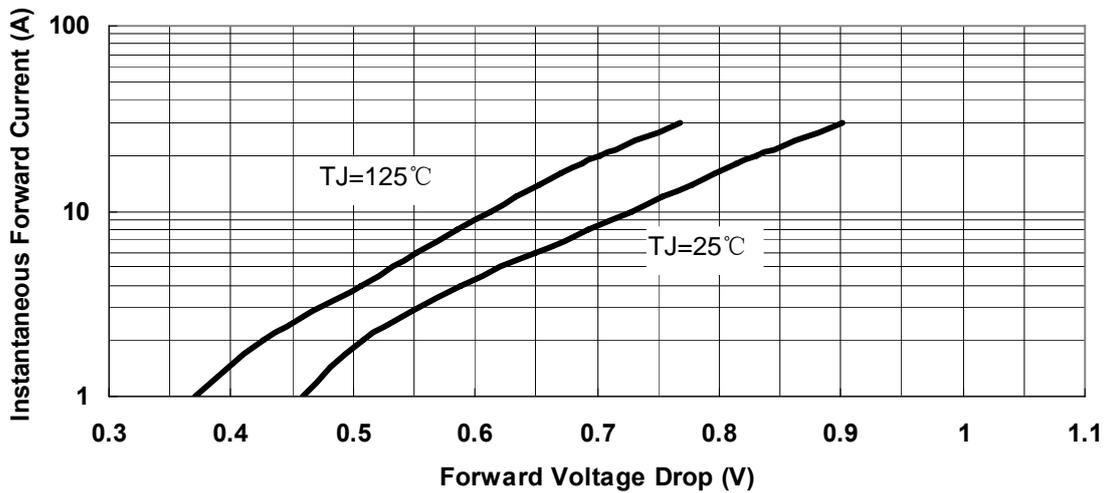


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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